



Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	2Ω @ V _{GS} = 5.0V	340mA
000	2.5Ω @ V _{GS} = 2.5V	300mA

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Motor Control
- Power Management Functions
- Backlighting

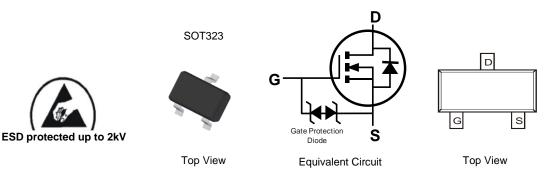
N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42
 Leadframe. Solderable per MIL-STD-202, Method 208⁽²⁾
- Weight: 0.006 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN61D9UW-7	SOT323	3,000/Tape & Reel
DMN61D9UW-13	SOT323	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

1A C	ΥM

1AC= Product Type Marking Code YM = Date Code Marking

Y or \overline{Y} = Year (ex: C = 2015)

M = Month (ex: 9 = September)

Date Code Key

Date Code r	Ney											
Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	В	С	D	E	F	G	Н	I	J	K	L	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	60	V	
Gate-Source Voltage		V _{GSS}	±20	V	
	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	340 270	mA
Continuous Drain Current (Note 6) $V_{GS} = 5.0V$	t<5s $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		ID	400 300	mA
Maximum Continuous Body Diode Forward Curren	t (Note 6)	ls	0.4	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	I _{DM}	1.2	А		

Thermal Characteristics	$(@T_A = +25^{\circ}C, unless otherwise specified.)$
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Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	320	mW	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	393	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<5s	R _{θJA}	306	C/VV	
Total Power Dissipation (Note 6)		PD	440	mW	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	289	°C/W	
Thermal Resistance, Junction to Amblent (Note 6)	t<5s	R _{0JA}	235	C/W	
Operating and Storage Temperature Range		T _{J.} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

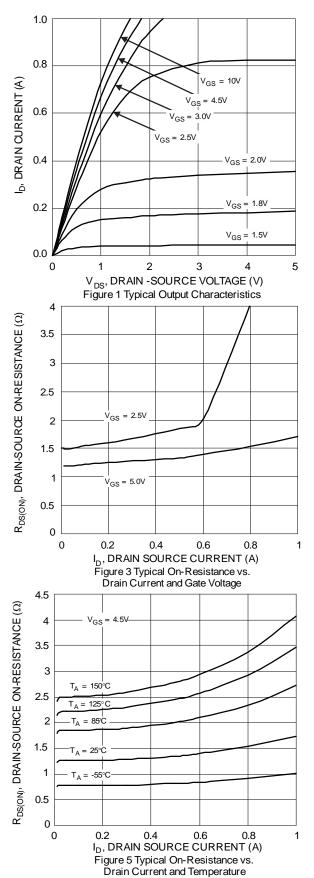
			_			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						1
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	_	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current	I _{DSS}			1.0	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	IGSS	_	_	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	_	1.0	V	$V_{DS} = 10V, I_D = 250\mu A$
			1.2	2.0		$V_{GS} = 5.0V, I_D = 0.05A$
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.6	2.5	Ω	$V_{GS} = 2.5V, I_D = 0.05A$
			2.5	3.5		V _{GS} = 1.8V, I _D = 0.05A
Forward Transconductance	Y _{fs}	200			mS	V _{DS} =10V, I _D = 0.2A
Diode Forward Voltage	V _{SD}	-	0.75	1.4	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		28.5	_	pF	
Output Capacitance	Coss		3.9	—	pF	V _{DS} = 30V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss		2.5	_	pF	1 = 1.000112
Gate Resistance	Rq	_	65	_	Ω	f = 1MHz , V _{GS} = 0V, V _{DS} = 0V
Total Gate Charge	Qg	_	0.4	—	nC	N/ A 51/ 1/ A 61/
Gate-Source Charge	Q _{qs}	—	0.1	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Drain Charge	Q _{gd}	_	0.1	_	nC	I _D = 250mA
Turn-On Delay Time	t _{D(ON)}	—	2.1		ns	
Turn-On Rise Time	t _R		1.8	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$
Turn-Off Delay Time	t _{D(OFF)}		14.4	_	ns	$R_{G} = 25\Omega, I_{D} = 200 \text{mA}$
Turn-Off Fall Time	t _F	—	8.4	—	ns]

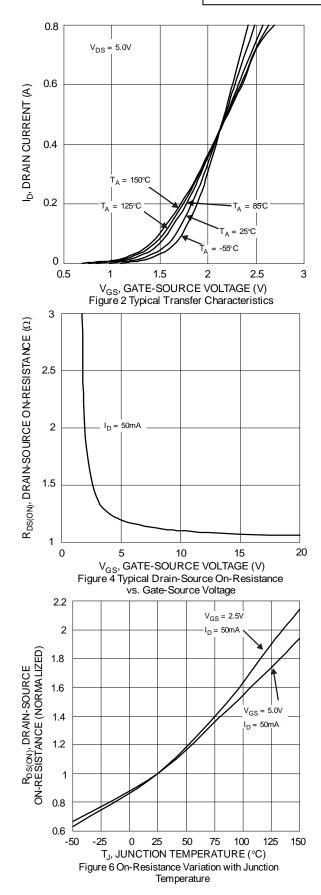
Notes:

Device mounted on FR-4 PCB, with minimum recommended pad layout.
 Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

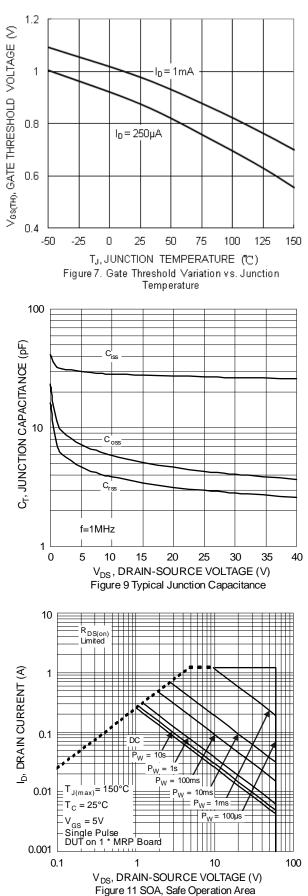


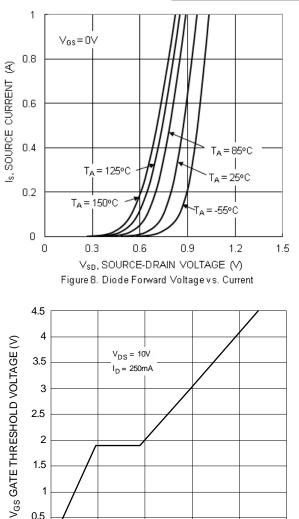


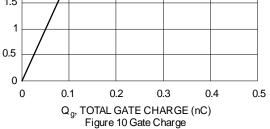


NEW PRODUCT

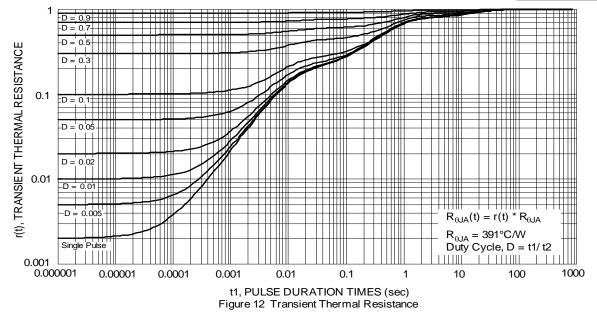






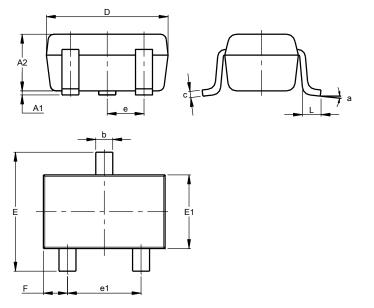






Package Outline Dimensions

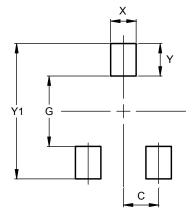
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT323									
Dim	Min	Min Max Typ							
A1	0.00	0.10	0.05						
A2	0.90	1.00	0.95						
b	0.25	0.40	0.30						
Ċ	0.10	0.18	0.11						
D	1.80	2.20	2.15						
ш	2.00	2.20	2.10						
E1	1.15	1.35	1.30						
e	C).650 B	SC						
e1	1.20	1.40	1.30						
F	0.375	0.475	0.425						
L	0.25	0.40	0.30						
а		8°							
All	Dimen	sions i	in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500



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